

L Number	Hits	Search Text	DB	Time stamp
-	138	257/410.ccls. and (silicide or silicate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 14:56
-	35	257/410.ccls. and (silicate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/07 14:56
-	231	257/411.ccls. and (gate near3 (silicon or silicate or silicide or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:49
-	298	257/411.ccls. and (gate or insulator or insulating) near3 (silicon or silicate or silicide or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:57
-	27	257/411.ccls. and (gate or insulator or insulating) near3 ((silicon or silicate or silicide or si) and (metal or tungsten or hafnium or zirconium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 09:01
-	110	257/411.ccls. and (insulator or insulating or dielectric) near3 (metal or tungsten or hafnium or zirconium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:25
-	15694	gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:31
-	3851	gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:35
-	3291	gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon with (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:39
-	1493	257/\$.ccls. and (gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near oxide or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZRSiON or Zr near2 SiON) with silicon with (metal near oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 10:39

-	73	gate near3 (dielectric or insulating or insulator or oxide) and (dielectric or insulating or insulator or oxide) near5 (metal near2 oxynitride or metal near2 oxy-nitride or metal near3 silicate or metal near3 silicide or hafnium near2 oxynitride or zirconium near2 oxynitride or HfSiON or Hf near2 SiON or ZrSiON or Zr near2 SiON) with silicon with (metal near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:25
-	7	gate near3 (dielectric or insulating or insulator or oxide) near6 (metal near2 silicate or hafnium near2 silicate or zirconium near2 silicate or HfSiON or HfSiO or ZrSiON or ZrSiO) near6 (metal adj oxide or TaO or TiO or HfO or ZrO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:29
-	26	gate near3 (dielectric or insulating or insulator or oxide) near6 (metal near2 silicate or hafnium near2 silicate or zirconium near2 silicate or HfSiON or HfSiO or ZrSiON or ZrSiO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:41
-	733	gate near3 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near4 (material or composition or concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:45
-	388	gate near2 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near2 (material or composition or concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 12:48
-	217	257/\$.ccls. and (gate near2 (dielectric or insulating or insulator or oxide) near3 (different or second or nonequal or differing or differ) near2 (material or composition or concentration) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 13:55
-	162	gate near2 (dielectric or oxide or insulator or insulating or insulative) near4 ((metal or metallic or tantalum or titanium or hafnium or zirconium) and silicon and (oxygen or oxide or dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 14:19
-	289	(257/410.ccls. or 257/411.ccls.) and (metal adj oxide or metallic adj oxide or tantalum adj oxide or tungsten adj oxide or titanium adj oxide or zirconium adj oxide or hafnium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 14:21
-	57	(257/410.ccls. or 257/411.ccls.) and (metal adj oxide or metallic adj oxide or tantalum adj oxide or tungsten adj oxide or titanium adj oxide or zirconium adj oxide or hafnium adj oxide) near2 (insulator or insulating or insulative or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 14:24